



BSS84

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) max}	I _D Τ _A = +25°C
-50V	10Ω @ V _{GS} = -5V	-130mA

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BSS84Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

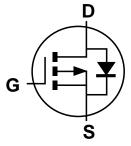
Mechanical Data

- Case: SOT23
- Case Material: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (Lead Free Plating) Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.009 grams (Approximate)

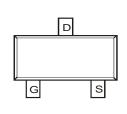








Equivalent Circuit



Top View

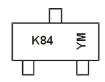
Ordering Information (Note 4)

	Part Number	Qualification	Case	Packaging
	BSS84-7-F	Commercial	SOT23	3000/Tape & Reel
	BSS84Q-7-F	Automotive	SOT23	3000/Tape & Reel
Г	BSS84-13-F	Commercial	SOT23	10000/Tape & Reel
Г	BSS84Q-13-F	Automotive	SOT23	10000/Tape & Reel

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

Marking Information



 $\begin{array}{l} \text{K84} = \underbrace{\text{Product Type Marking Code}} \\ \text{YM or } \overline{\text{Y}} \text{M= Date Code Marking} \\ \text{Y or } \overline{\text{Y}} = \text{Year (ex: G = 2019)} \\ \text{M = Month (ex: 9 = September)} \\ \end{array}$

Date Code Key

	Year	1998	2	2016	20	17	2018	2019	2020	202	21 2	2022	2023
	Code	J	ı	D	E		F	G	Η	- 1		J	K
Γ	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \le 20k\Omega$		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 5)	Continuous	Ι _D	-130	mA
Pulsed Drain Current		I _{DM}	-1.2	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

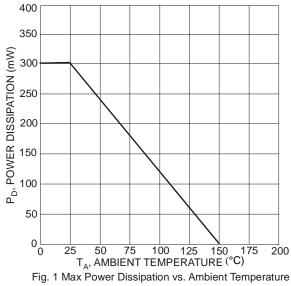
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	-50	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
		_	_	-1	μA	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = +25$ °C	
Zero Gate Voltage Drain Current	I_{DSS}	_	_	-2	μΑ	$V_{DS} = -50V$, $V_{GS} = 0V$, $T_{J} = +125$ °C	
		_	—	-100	nA	$V_{DS} = -25V$, $V_{GS} = 0V$, $T_{J} = +25$ °C	
Gate-Body Leakage	I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.8	_	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	10	Ω	$V_{GS} = -5V, I_D = -0.100A$	
Forward Transconductance	g FS	0.05	_	_	S	$V_{DS} = -25V$, $I_{D} = -0.1A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	24.6	45	pF		
Output Capacitance	Coss	_	4.7	25	pF	$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Reverse Transfer Capacitance	C _{rss}	_	2.8	12	pF		
Gate Resistance	R_g	_	916	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	0.28	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	0.59	_	nC	V 40V I 0.4A	
Gate-Source Charge	Qgs	_	0.09	_	nC	$V_{DS} = -10V, I_{D} = -0.1A$	
Gate-Drain Charge	Q_{gd}	_	0.08	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	10	_	ns	$V_{DD} = -30V$, $I_D = -0.27A$,	
Turn-Off Delay Time	t _{D(OFF)}		18	_	ns	$R_{GEN} = 50\Omega$, $V_{GS} = -10V$	

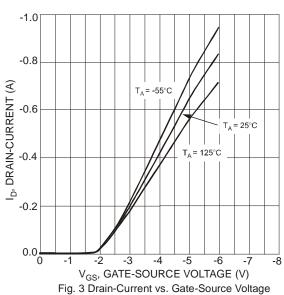
Notes: 5. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.

^{6.} Short duration pulse test used to minimize self-heating effect.

^{7.} Guaranteed by design. Not subject to production testing.







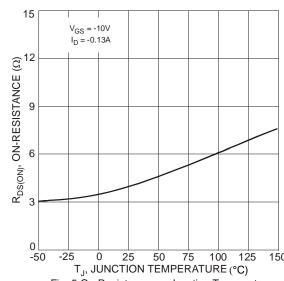


Fig. 5 On-Resistance vs. Junction Temperature

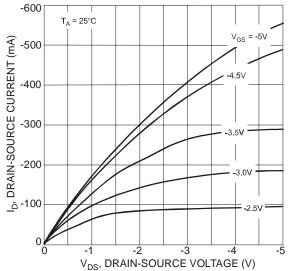


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

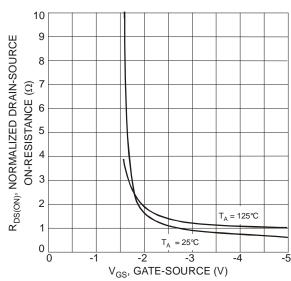


Fig. 4 On-Resistance vs. Gate-Source Voltage

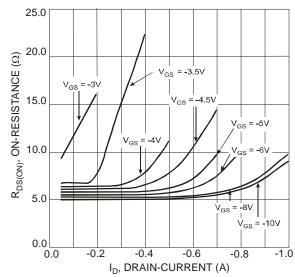


Fig. 6 On-Resistance vs. Drain-Current





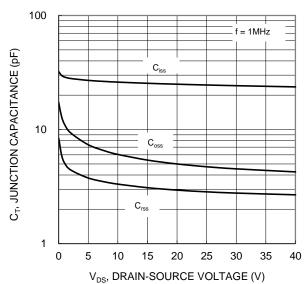
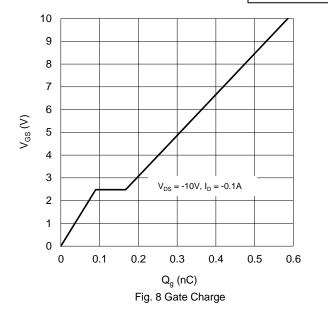


Fig. 7 Typical Junction Capacitance 10 R_{DS(ON)} Limited ID, DRAIN CURRENT (A) 1 0.1 P_W = 100ms $T_{J(Max)} = 150$ °C $T_C = 25$ °C Single Pulse DUT on 1*MRP 0.01 Board V_{GS} = -10V 0.001 0.1 1 10 100

V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig. 9 SOA, Safe Operation Area

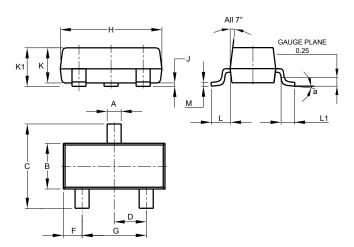




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

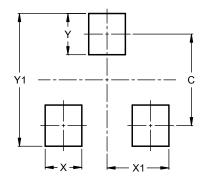


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	29



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